

Code: 9A04605

Time: 3 hours

R09

Max Marks: 70

B.Tech III Year II Semester (R09) Supplementary Examinations December/January 2015/2016 **VLSI DESIGN**

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(Common to ECE, EIE and E.Con.E)

Answer any FIVE questions
All questions carry equal marks

- 1 (a) What is SOI process? Explain clearly about the advantages and disadvantages of it.
 - (b) Write about floating body voltage.
- 2 (a) Explain the Tunneling mechanism in MOS devices.
 - (b) How does the transistor characteristics are influenced by the temperature?
- 3 Design a layout diagram for two input NMOS NOR gate.
- 4 (a) Realize the logic function [(AB)+(CD)] using compound gates.
 - (b) Realize the logic function $x_1^1 + x_2^1 x_3^1$ using compound gates.
- 5 (a) Write about switch logic and hence compare the properties of pass transistor and transmission gate used as switches in NMOS and CMOS respectively.
 - (b) Implement 8:1 multiplexers using CMOS switch logic.
- 6 (a) Explain about the designing of a chip with sea of gates (SOG).
 - (b) Write about FPGA.
- What is meant by logic synthesis? Explain in detail the advantages and disadvantages of network restructuring in order to obtain logic optimization.
- 8 (a) Differentiate between chip level test techniques and system level techniques.
 - (b) Explain any one of the chip level and system level methods.
